

Appl. No. 10/010,548  
Amdt. dated November 26, 2003  
Reply to Office Action of August 29, 2003

### AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listing, of claims in the application:

#### Listing of Claims:

1. (Currently Amended) A method of etching a semiconductor device using a neutral beam comprising:  
extracting an ion beam having a predetermined polarity from an ion source to accelerate the ion beam such that an incident angle of the ion beam is in a range of 75 - 85° from a vertical line to a horizontal surface of a reflector;  
reflecting an accelerated ion beam by at the reflector to neutralize the reflected ion beam; and  
positioning a substrate to be etched in a path of a neutral beam to etch a material layer on the substrate with the neutral beam.
- 2-3. (Canceled).
4. (Currently Amended) The method of claim 31, further comprising adjusting a gradient of the reflector to an incident ion beam.
5. (Currently Amended) The method of claim 31, further comprising applying a voltage to the reflector to adjust a path of an incident ion beam.
6. (Previously Presented) The method of claim 1, wherein the reflector is selected from the group consisting of a semiconductor substrate, a silicon dioxide substrate and a metal substrate.
- 7-17. (Canceled)